### **DALLAS** SEMICONDUCTOR

### DS1646/DS1646P Nonvolatile Timekeeping RAM

#### FEATURES

- Integrated NV SRAM, real time clock, crystal, powerfail control circuit and lithium energy source
- Clock registers are accessed identical to the static RAM. These registers are resident in the eight top RAM locations.
- Totally nonvolatile with over 10 years of operation in the absence of power
- Access times of 120 ns and 150 ns
- BCD coded year, month, date, day, hours, minutes, and seconds with leap year compensation valid up to 2100
- $\bullet$  Power–fail write protection allows for  $\pm 10\%\,V_{CC}$  power supply tolerance
- DS1646 only (DIP Module)
  - Standard JEDEC Byte-wide 128K x 8 RAM pinout
- DS1646P only (PowerCap Module Board)
  - Surface mountable package for direct connection to PowerCap containing battery and crystal
  - Replaceable battery (PowerCap)
  - Power-fail output
  - Pin–for–pin compatible with other densities of DS164XP Timekeeping RAM

#### **ORDERING INFORMATION**

•	-120	120 ns access
	-150	150 ns access

\*DS1646P-XXX 34-pin PowerCap Module Board

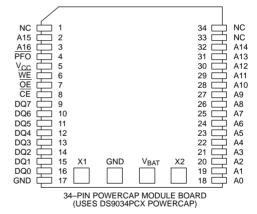
-	-120	120 ns access
	-150	150 ns access

\*DS9034PCX (PowerCap) Required; must be ordered separately

#### **PIN ASSIGNMENT**

NC	01	32 🛛	V <sub>CC</sub>
A16	02	31 🛽	A15
A14	03	30 🛛	NC
A12	04	29	WE
A7	05	28	A13
A6	06	27	A8
A5	07	26	A9
A4	8	25	A11
A3	09	24	OE
A2	<b>1</b> 0	23	A10
A1	0 11	22	CE
A0	012	21	DQ7
DQ0	<b>1</b> 3	20	DQ6
DQ1	014	19	DQ5
DQ2	<b>1</b> 5	18	DQ4
GND	<b>1</b> 6	17 🛛	DQ3

32-PIN ENCAPSULATED PACKAGE



#### **PIN DESCRIPTION**

A0–A16	<ul> <li>Address Input</li> </ul>
CE	<ul> <li>Chip Enable</li> </ul>
OE	<ul> <li>Output Enable</li> </ul>
WE	<ul> <li>Write Enable</li> </ul>
V <sub>CC</sub>	<ul> <li>+5 Volts</li> </ul>
GND	<ul> <li>Ground</li> </ul>
DQ0–DQ7	<ul> <li>Data Input/Output</li> </ul>
NC	<ul> <li>No Connect</li> </ul>
PFO	<ul> <li>Power–Fail Output (DS1646P only)</li> </ul>
X1, X2	<ul> <li>Crystal Connection</li> </ul>
V <sub>BAT</sub>	<ul> <li>Battery Connection</li> </ul>

#### DESCRIPTION

The DS1646 is a 128K x 8 nonvolatile static RAM with a full function Real Time Clock (RTC) which are both accessible in a Byte-wide format. The nonvolatile timekeeping RAM is function equivalent to any JEDEC standard 128K x 8 SRAM. The device can also be easily substituted in ROM. EPROM and EEPROM sockets providing read/write nonvolatility and the addition of the real time clock function. The real time clock information resides in the eight uppermost RAM locations. The RTC registers contain year, month, date, day, hours, minutes, and seconds data in 24-hour BCD format. Corrections for the day of the month and leap year are made automatically. The RTC clock registers are double buffered to avoid access of incorrect data that can occur during clock update cycles. The double buffered system also prevents time loss as the timekeeping countdown continues unabated by access to time register data. The DS1646 also contains its own power-fail circuitry which deselects the device when the  $V_{CC}$  supply is in an out of tolerance condition. This feature prevents loss of data from unpredictable system operation brought on by low V<sub>CC</sub> as errant access and update cvcles are avoided.

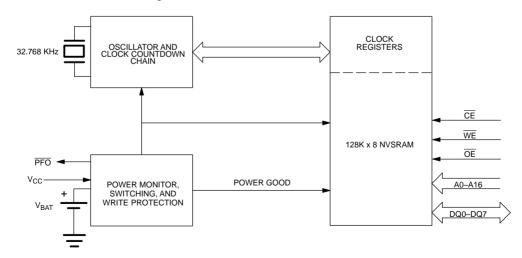
#### PACKAGES

The DS1646 is available in two packages (32–pin DIP module and 34–pin PowerCap module). The 32–pin Dip style module integrated the crystal, lithium energy source, and silicon all in one package. The 34–pin PowerCap Module Board is designed with contacts for con-

nection to a separate PowerCap (DS9034PCX) that contains the crystal and battery. This desgin allows the PowerCap to be mounted on top of the DS1646P after the completion of the surface mount process. Mounting the PowerCap after the surface mount process prevents damage to the crystal and battery due to high temperatures required for solder reflow. The PowerCap is keyed to prevent reverse insertion. The PowerCap Module Board and PowerCap are ordered separately and shipped in seperate containers. The part number for the PowerCap is DS9034PCX.

# CLOCK OPERATIONS-READING THE CLOCK

While the double buffered register structure reduces the chance of reading incorrect data, internal updates to the DS1646 clock registers should be halted before clock data is read to prevent reading of data in transition. However, halting the internal clock register updating process does not affect clock accuracy. Updating is halted when a one is written into the read bit, the seventh most significant bit in the control register. As long as a one remains in that position, updating is halted. After a halt is issued, the registers reflect the count, that is day, date, and time that was current at the moment the halt command was issued. However, the internal clock registers of the double buffered system continue to update so that the clock accuracy is not affected by the access of data. All of the DS1646 registers are updated simultaneously after the clock status is reset. Updating is within a second after the read bit is written to zero.



#### BLOCK DIAGRAM DS1646 Figure 1

V <sub>CC</sub>	CE	OE	WE	MODE	DQ	POWER
	V <sub>IH</sub>	Х	Х	DESELECT	HIGH–Z	STANDBY
	Х	Х	Х	DESELECT	HIGH–Z	STANDBY
$5 \text{ VOLTS} \pm 10\%$	$V_{IL}$	Х	V <sub>IL</sub>	WRITE	DATA IN	ACTIVE
	$V_{IL}$	$V_{IL}$	V <sub>IH</sub>	READ	DATA OUT	ACTIVE
	$V_{IL}$	V <sub>IH</sub>	V <sub>IH</sub>	READ	HIGH–Z	ACTIVE
<4.5 VOLTS >V <sub>BAT</sub>			HIGH–Z	CMOS STANDBY		
<v<sub>BAT</v<sub>	Х	Х	Х	DESELECT	HIGH–Z	DATA RETENTION MODE

#### TRUTH TABLE DS1646 Table 1

#### SETTING THE CLOCK

The eighth bit of the control register is the write bit. Setting the write bit to a one, like the read bit, halts updates to the DS1646 registers. The user can then load them with the correct day, date and time data in 24–hour BCD format. Resetting the write bit to a zero then transfers those values to the actual clock counters and allows normal operation to resume.

# STOPPING AND STARTING THE CLOCK OSCILLATOR

The clock oscillator may be stopped at any time. To increase the shelf life, the oscillator can be turned off to minimize current drain from the battery. The  $\overrightarrow{OSC}$  bit is the MSB for the seconds registers. Setting it to a 1 stops the oscillator.

#### FREQUENCY TEST BIT

Bit 6 of the day byte is the frequency test bit. When the frequency test bit is set to logic "1" and the oscillator is

running, the LSB of the seconds register will toggle at 512 Hz. When the seconds register is being read, the DQ0 line will toggle at the 512 Hz frequency as long as conditions for access remain valid (i.e.,  $\overline{CE}$  low,  $\overline{OE}$  low, and address for seconds register remain valid and stable).

#### **CLOCK ACCURACY (DIP MODULE)**

The DS1646 is guaranteed to keep time accuracy to within  $\pm 1$  minute per month at 25°C.

#### CLOCK ACCURACY (POWERCAP MODULE)

The DS1646P and DS9034PCX are each individually tested for accuracy. Once mounted together, the module is guaranteed to keep time accuracy to within  $\pm 1.53$  minutes per month (35 ppm) at 25°C.

			FUNCTION							
ADDRESS	B <sub>7</sub>	B <sub>6</sub>	$B_5$	B <sub>4</sub>	B <sub>3</sub>	B <sub>2</sub>	B <sub>1</sub>	B <sub>0</sub>	FUNCT	UN
1FFFF	-	-	-	-	-	-	-	-	YEAR	00–99
1FFFE	Х	Х	Х	-	_	-	_	_	MONTH	01–12
1FFFD	Х	Х	-	-	-	-	-	-	DATE	01–31
1FFFC	х	FT	Х	Х	Х	-	-	-	DAY	01–07
1FFFB	Х	Х	-	-	-	-	-	_	HOUR	00–23
1FFFA	х	-	-	-	-	-	-	-	MINUTES	00–59
1FFF9	OSC	-	-	-	_	-	_	_	SECONDS	00–59
1FFF8	W	R	Х	Х	Х	Х	Х	Х	CONTROL	А
OSC = STOP BIT     R = READ BIT     FT =       W = WRITE BIT     X = UNUSED								FREQUEN	CY TEST	

#### DS1646 REGISTER MAP – BANK1 Table 2

#### NOTE:

All indicated "X" bits are not dedicated to any particular function and can be used as normal RAM bits.

#### **RETRIEVING DATA FROM RAM OR CLOCK**

The DS1646 is in the read mode whenever WE (write enable) is high, CE (chip enable) is low. The device architecture allows ripple-through access to any of the address locations in the NVSRAM. Valid data will be available at the DQ pins within tAA after the last address input is stable, providing that the CE and OE access times and states are satisfied. If CE or OE access times are not met, valid data will be available at the latter of chip enable access (t<sub>CEA</sub>) or at output enable access time (t<sub>OEA</sub>). The state of the data input/output pins (DQ) is controlled by CE and OE. If the outputs are activated before t<sub>AA</sub>, the data lines are driven to an intermediate state until tAA. If the address inputs are changed while CE and OE remain valid, output data will remain valid for output data hold time  $(t_{OH})$  but will then go indeterminate until the next address access.

#### WRITING DATA TO RAM OR CLOCK

The DS1646 is in the write mode whenever  $\overline{WE}$  and  $\overline{CE}$  are in their active state. The start of a write is referenced to the latter occurring high to low transition of  $\overline{WE}$  and  $\overline{CE}$ . The addresses must be held valid throughout the cycle.  $\overline{CE}$  or  $\overline{WE}$  must return inactive for a minimum of t<sub>WR</sub> prior to the initiation of another read or write cycle.

Data in must be valid  $t_{DS}$  prior to the end of write and remain valid for  $t_{DH}$  afterward. In a typical application, the  $\overline{OE}$  signal will be high during a write cycle. However,  $\overline{OE}$  can be active provided that care is taken with the data bus to avoid bus contention. If  $\overline{OE}$  is low prior to  $\overline{WE}$  transitioning low the data bus can become active with read data defined by the address inputs. A low transition on  $\overline{WE}$  will then disable the outputs  $t_{WEZ}$  after  $\overline{WE}$  goes active.

#### DATA RETENTION MODE

When  $V_{CC}$  is within nominal limits ( $V_{CC} > 4.5$  volts) the DS1646 can be accessed as described above with read or write cycles. However, when  $V_{CC}$  is below the power–fail point  $V_{PF}$  (point at which write protection occurs) the internal clock registers and RAM are blocked from access. This is accomplished internally by inhibiting access via the  $\overline{CE}$  signal. At this time the power–fail output signal ( $\overline{PFO}$ ) will be driven active low and will remain active until  $V_{CC}$  returns to nominal levels. When  $V_{CC}$  falls below the level of the internal battery supply, power input is switched from the  $V_{CC}$  pin to the internal battery and clock activity, RAM, and clock data are maintained from the battery until  $V_{CC}$  is returned to nominal level.

#### **ABSOLUTE MAXIMUM RATINGS\***

Voltage on Any Pin Relative to Ground Operating Temperature Storage Temperature Soldering Temperature -0.3V to +7.0V 0°C to 70°C -20°C to +70°C 260°C for 10 seconds (See Note 7)

\* This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operation sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods of time may affect reliability.

#### **RECOMMENDED DC OPERATING CONDITIONS**

(0°C to 70°C)

PARAMETER	SYMBOL	MIN	ТҮР	MAX	UNITS	NOTES
Supply Voltage	V <sub>CC</sub>	4.5	5.0	5.5	V	1
Logic 1 Voltage All Inputs	VIH	2.2		V <sub>CC</sub> +0.3	V	
Logic 0 Voltage All Inputs	V <sub>IL</sub>	-0.3		0.8	V	

#### DC ELECTRICAL CHARACTERISTICS

 $(0^{\circ}C \le t_A \le 70^{\circ}C; V_{CC}=5.0V \pm 10\%)$ 

PARAMETER	SYMBOL	MIN	TYP	MAX	UNITS	NOTES
Average V <sub>CC</sub> Power Supply Current	I <sub>CC1</sub>			85	mA	2, 3
TTL Standby Current ( $\overline{CE} = V_{IH}$ )	I <sub>CC2</sub>		3	6	mA	2, 3
CMOS Standby Current (CE=V <sub>CC</sub> -0.2V)	I <sub>CC3</sub>		2	4.0	mA	2, 3
Input Leakage Current (any input)	۱ <sub>IL</sub>	-1		+1	μΑ	
Output Leakage Current	I <sub>OL</sub>	-1		+1	μΑ	
Output Logic 1 Voltage (I <sub>OUT</sub> = -1.0 mA)	V <sub>OH</sub>	2.4			V	
Output Logic 0 Voltage (I <sub>OUT</sub> = +2.1 mA)	V <sub>OL</sub>			0.4	V	
Write Protection Voltage	V <sub>PF</sub>	4.0	4.25	4.5	V	

AC ELECTRICAL CHARACTERISTICS					$(0^{\circ}C \text{ to } 70^{\circ}C; V_{CC} = 5.0V + 10\%)$				
	CVMDOI	DS1646–120		DS1646-150					
PARAMETER	SYMBOL	MIN	MAX	MIN	MAX	UNITS	NOTES		
Read Cycle Time	t <sub>RC</sub>	120		150		ns			
Address Access Time	t <sub>AA</sub>		120		150	ns			
CE Access Time	t <sub>CEA</sub>		120		150	ns			
CE Data Off Time	t <sub>CEZ</sub>		40		50	ns			
Output Enable Access Time	t <sub>OEA</sub>		100		120	ns			
Output Enable Data Off Time	t <sub>OEZ</sub>		40		50	ns			
Output Enable to DQ Low-Z	t <sub>OEL</sub>	5		5		ns			
CE to DQ Low-Z	t <sub>CEL</sub>	5		5		ns			
Output Hold from Address	t <sub>OH</sub>	5		5		ns			
Write Cycle Time	t <sub>WC</sub>	120		150		ns			
Address Setup Time	t <sub>AS</sub>	0		0		ns			
CE Pulse Width	t <sub>CEW</sub>	100		120		ns			
Address Hold from End of Write	t <sub>AH1</sub> t <sub>AH2</sub>	5 30		5 30		ns ns	5 6		
Write Pulse Width	t <sub>WEW</sub>	75		90		ns			
WE Data Off Time	t <sub>WEZ</sub>		40		50	ns			
$\overline{\text{WE}} \text{ or } \overline{\text{CE}}$ Inactive Time	t <sub>WR</sub>	10		10		ns			
Data Setup Time	t <sub>DS</sub>	85		110		ns			
Data Hold Time High	t <sub>DH1</sub> t <sub>DH2</sub>	0 25		0 25		ns ns	5 6		

#### AC TEST CONDITIONS

0V to 3V Input Levels: Transition Times: 5 ns

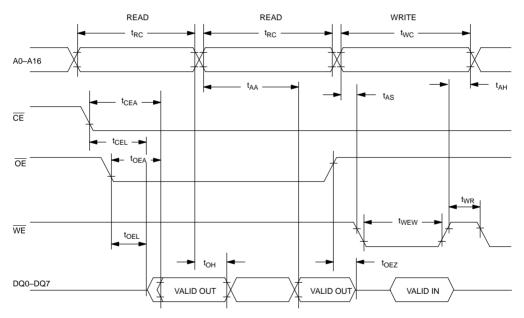
#### CAPACITANCE

(t<sub>A</sub> = 25°C)

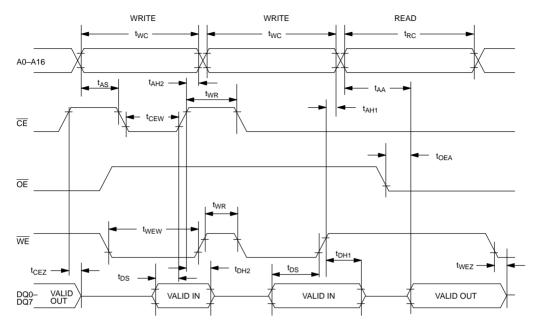
PARAMETER	SYMBOL	MIN	ТҮР	MAX	UNITS	NOTES
Capacitance on all pins (except DQ)	CI			7	pF	
Capacitance on DQ pins	C <sub>DQ</sub>			10	pF	

AC ELECTRICAL CHARACTE	(0°C to 70°C)					
PARAMETER	SYMBOL	MIN	ТҮР	MAX	UNITS	NOTES
$\overline{CE}$ or $\overline{WE}$ at V <sub>IH</sub> before Power– Down	t <sub>PD</sub>	0			μs	
V <sub>PF</sub> (Max) to V <sub>PF</sub> (Min) V <sub>CC</sub> Fall Time	t <sub>F</sub>	300			μs	
$\rm V_{PF}$ (Min) to $\rm V_{SO}$ $\rm V_{CC}$ Fall Time	t <sub>FB</sub>	10			μs	
$V_{\text{SO}}$ to $V_{\text{PF}}$ (Min) $V_{\text{CC}}$ Rise Time	t <sub>RB</sub>	1			μs	
$V_{\text{PF}}$ (Min) to $V_{\text{PF}}$ (Max) $V_{\text{CC}}$ Rise Time	t <sub>R</sub>	0			μs	
Power–Up	t <sub>REC</sub>	15	25	35	ms	
Expected Data Retention Time (Oscillator On)	t <sub>DR</sub>	10			years	4

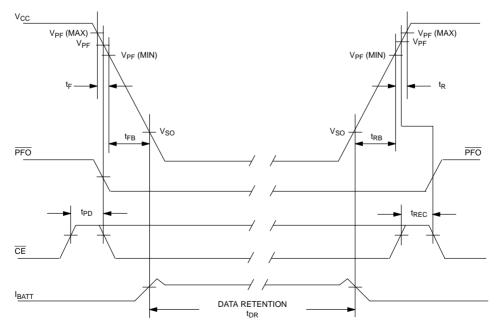
#### DS1646 READ CYCLE TIMING



#### **DS1646 WRITE CYCLE TIMING**



#### POWER-DOWN/POWER-UP TIMING



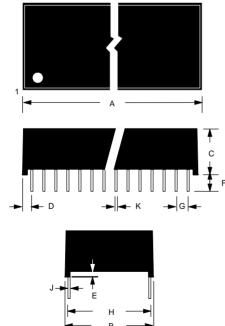
#### NOTES:

- 1. All voltages are referenced to ground.
- 2. Typical values are at 25°C and nominal supplies.
- 3. Outputs are open.
- 4. Data retention time is at 25°C and is calculated from the date code on the device package. The date code XXYY is the year followed by the week of the year in which the device was manufactured. For example, 9225, would mean the 25th week of 1992.
- 5.  $t_{AH1}$ ,  $t_{DH1}$  are measured from  $\overline{WE}$  going high.
- 6.  $t_{AH2}$ ,  $t_{DH2}$  are measured from  $\overline{CE}$  going high.
- Real–Time Clock Modules (DIP) can be successfully processed through conventional wave–soldering techniques as long as temperature exposure to the lithium energy source contained within does not exceed +85°C. Post solder cleaning with water washing techniques is acceptable, provided that ultrasonic vibration is not used.

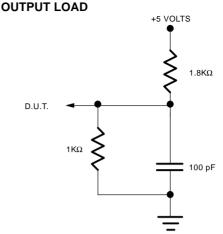
In addition, for the PowerCap version:

- a. Dallas Semiconductor recommends that PowerCap Module bases experience one pass through solder reflow oriented with the label side up ("live bug").
- b. Hand Soldering and touch up: Do not touch or apply the soldering iron to leads for more than 3 (three) seconds. To solder, apply flux to the pad, heat the lead frame pad and apply solder. To remove the part, apply flux, heat the lead frame pad until the solder reflows and use a solder wick to remove solder.

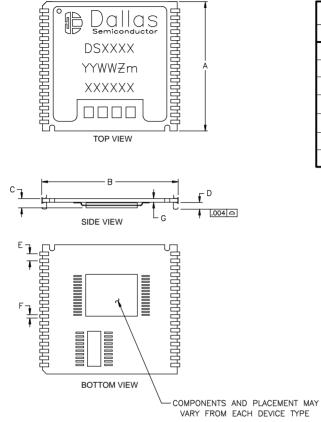
## DS1646 32-PIN PACKAGE



PKG	32-PIN	
DIM	MIN	MAX
A IN.	1.670	1.690
MM	38.42	38.93
B IN.	0.715	0.740
MM	18.16	18.80
C IN.	0.335	0.365
MM	8.51	9.27
D IN.	0.075	0.105
MM	1.91	0.67
E IN.	0.015	0.030
MM	0.38	0.76
F IN.	0.140	0.180
MM	3.56	4.57
G IN.	0.090	0.110
MM	2.29	2.79
H IN.	0.590	0.630
MM	14.99	16.00
J IN.	0.010	0.018
MM	0.25	0.45
K IN.	0.015	0.025
MM	0.38	0.64



#### DS1646P

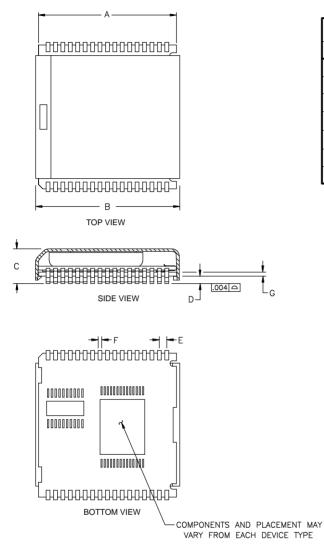


INCHES PKG DIM MIN NOM MAX 0.930 А 0.920 0.925 0.990 В 0.980 0.985 С \_ 0.080 \_ 0.058 D 0.052 0.055 F 0.048 0.050 0.052 F 0.020 0.015 0.025 G 0.025 0.027 0.030

NOTE: For the PowerCap version:

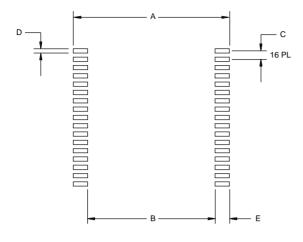
- a. Dallas Semiconductor recommends that PowerCap Module bases experience one pass through solder reflow oriented with the label side up ("live bug").
- b. Hand Soldering and touch up: Do not touch or apply the soldering iron to leads for more than 3 (three) seconds. To solder, apply flux to the pad, heat the lead frame pad and apply solder. To remove the part, apply flux, heat the lead frame pad until the solder reflows and use a solder wick to remove solder.

#### DS1646P WITH DS9034PCX ATTACHED



PKG	INCHES		
DIM	MIN	NOM	MAX
А	0.920	0.925	0.930
В	0.955	0.960	0.965
С	0.240	0.245	0.250
D	0.052	0.055	0.058
E	0.048	0.050	0.052
F	0.015	0.020	0.025
G	0.020	0.025	0.030

### RECOMMENDED POWERCAP MODULE LAND PATTERN



	INCHES			
PKG DIM	MIN	NOM	MAX	
А	-	1.050	-	
В	-	0.826	-	
С	-	0.050	-	
D	-	0.030	-	
E	-	0.112	-	